

PAT-NO: JP02000353702A
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TITLE: LOW PERMITTIVITY MULTIPLE CARBON CONTAINING
SILICON
OXIDE DIELECTRIC USED IN INTEGRATED CIRCUIT
STRUCTURE,
AND MANUFACTURE THEREOF
PUBN-DATE: December 19, 2000

INVENTOR-INFORMATION:

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ABSTRACT:

PROBLEM TO BE SOLVED: To obtain a carbon containing silicon oxide dielectric, having the permittivity lower than the permittivity of carbon containing a silicon oxide dielectric formed using methyl silane as the precursor of low permittivity.

SOLUTION: This are provided a plurality of carbon containing silicon oxide dielectrics of low permittivity used for an integrated circuit structure, comprising silicon oxide substance containing silicon atoms to be

connected to
a plurality of carbon containing radicals consisting of carbon atoms
and first
class hydrogen. Desirably, the plurality of carbon-containing
radicals have
the chemical formulae $(C)_y(CH_3)_2$. Here (y) in the chemical formula
indicates
the integral number of 1 to 4 for a branched alkyl radical, the
integral number
3 to 5 for an annular alkyl radical, (z) indicates $2y+1$ for the
branched alkyl
radical, and also (z) indicates $2y-1$ pertaining to the annular alkyl
radical.

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